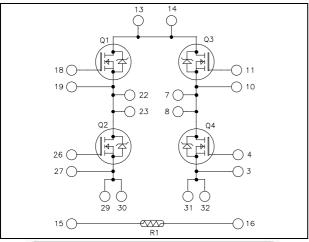
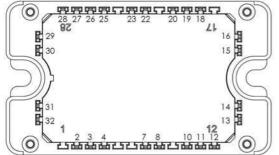


Full - Bridge MOSFET Power Module

$$\begin{split} V_{DSS} &= 1000 V \\ R_{DSon} &= 450 m \Omega \text{ typ @ Tj} = 25^{\circ} C \\ I_D &= 18 A \text{ @ Tc} = 25^{\circ} C \end{split}$$





All multiple inputs and outputs must be shorted together Example: 13/14; 29/30; 22/23 ...

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

Power MOS 7[®] FREDFETs

- Low R_{DSon}
- Low input and Miller capacitance
- Low gate charge
- Fast intrinsic reverse diode
- Avalanche energy rated
- Very rugged
- Kelvin source for easy drive
- Very low stray inductance
- Internal thermistor for temperature monitoring

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Each leg can be easily paralleled to achieve a phase leg of twice the current capability
- RoHS Compliant

All ratings @ $T_i = 25^{\circ}C$ unless otherwise specified

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V_{DSS}	Drain - Source Voltage		1000	V
Ţ	Continuous Drain Current	$T_c = 25^{\circ}C$	18	
I_D		$T_c = 80^{\circ}C$	14	A
I_{DM}	Pulsed Drain current		72	
V_{GS}	Gate - Source Voltage		±30	V
R _{DSon}	Drain - Source ON Resistance		540	mΩ
P_D	Power Dissipation	357	W	
I_{AR}	Avalanche current (repetitive and non repetitive)		18	A
E _{AR}	Repetitive Avalanche Energy		50	I
E_{AS}	Single Pulse Avalanche Energy		2500	mJ

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.



Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 1000V$			100	μΑ
R _{DS(on)}	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 9A$		450	540	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 2.5 \text{mA}$	3		5	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$			±150	nA

Dynamic Characteristics

•	Characteristics	T4 C 1:4:	14:	T	14	T74
	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V$		4350		
C_{oss}	Output Capacitance	$V_{DS} = 25V$		715		pF
C_{rss}	Reverse Transfer Capacitance	f = 1MHz		120		
$Q_{\rm g}$	Total gate Charge	$V_{GS} = 10V$		154		
Q_{gs}	Gate – Source Charge	$V_{Bus} = 500V$		26		пC
Q_{gd}	Gate – Drain Charge	$I_D = 18A$		97		
$T_{d(on)}$	Turn-on Delay Time	Inductive switching @ 125°C		10		
T_{r}	Rise Time	$V_{GS} = 15V$		12		ns
$T_{d(off)}$	Turn-off Delay Time	$\begin{array}{c} \begin{array}{c} \begin{array}{c} \begin{array}{c} \\ \\ \end{array} \end{array} \\ \begin{array}{c} I_D = 18A \end{array}$		121		
T_{f}	Fall Time	$R_G = 5\Omega$		35		
Eon	Turn-on Switching Energ	Inductive switching @ 25°C		639		
E _{off}	Turn-off Switching Energy	$V_{GS} = 15V, V_{Bus} = 667V$ $I_D = 18A, R_G = 5\Omega$		380		μJ
Eon	Turn-on Switching Energy	Inductive switching @ 125°C $V_{GS} = 15V, V_{Bus} = 667V$ $I_D = 18A, R_G = 5\Omega$		1046		_
E _{off}	Turn-off Switching Energy			451		μJ
R_{thJC}	Junction to Case Thermal Resistance	2			0.35	°C/W

Source - Drain diode ratings and characteristics

Source Drain aloue ratings and characteristics								
Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit	
I_S	Continuous Source current		$Tc = 25^{\circ}C$			18		
	(Body diode)		$Tc = 80^{\circ}C$			14	Α	
V_{SD}	Diode Forward Voltage	$V_{GS} = 0V, I_S = -18A$	\			1.3	V	
dv/dt	Peak Diode Recovery •					18	V/ns	
t _{rr}	Daviana Dagayany Tima	$I_{S} = -18A$ $V_{R} = 667V$	$T_j = 25$ °C			340	***	
	Reverse Recovery Time		$T_j = 125$ °C			640	ns	
Qrr	Reverse Recovery Charge	$di_{S}/dt = 100A/\mu s$	$T_j = 25$ °C		1.78			
			$T_j = 125$ °C		4.47		μС	

• dv/dt numbers reflect the limitations of the circuit rather than the device itself.

 $I_S \leq \text{--} \ 18A \qquad di/dt \leq 700 A/\mu s \qquad V_R \leq V_{DSS} \qquad T_j \leq 150 ^{\circ} C$



Thermal and package characteristics

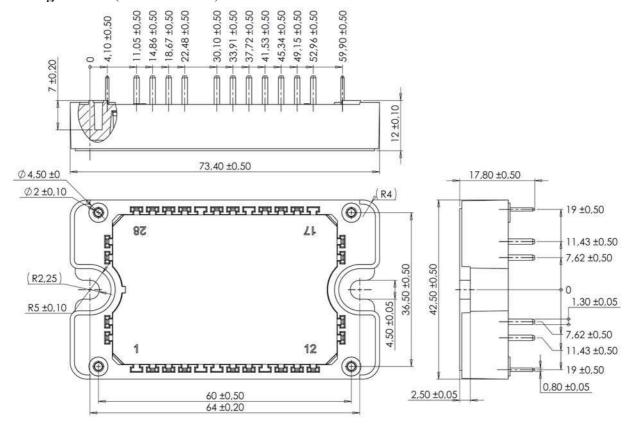
Symbol	Characteristic			Min	Max	Unit
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000		V
$T_{\rm J}$	Operating junction temperature range			-40	150	
T_{JOP}	Recommended junction temperature under switching conditions			-40	T _J max - 25	°C
T_{STG}	Storage Temperature Range			-40	125	
$T_{\rm C}$	Operating Case Temperature			-40	125	
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight				110	g

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic		Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C	25°C		50		kΩ
$\Delta R_{25}/R_{25}$				5		%
$B_{25/85}$	$T_{25} = 298.15 \text{ K}$			3952		K
$\Delta B/B$		T _C =100°C		4		%

$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]} \quad \begin{array}{l} \text{T: Thermistor temperature} \\ R_T: \text{ Thermistor value at T} \end{array}$$

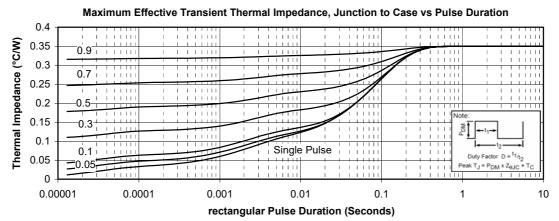
Package outline (dimensions in mm)

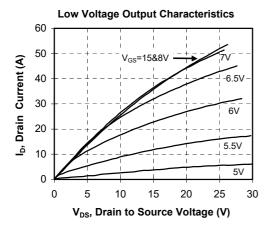


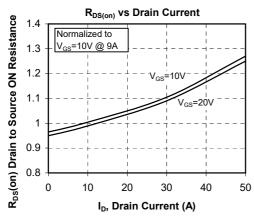
See application note 1906 - Mounting Instructions for SP3F Power Modules on $\underline{www.microsemi.com}$

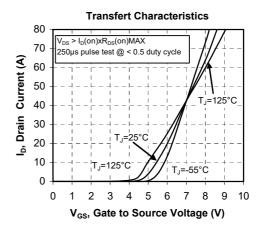


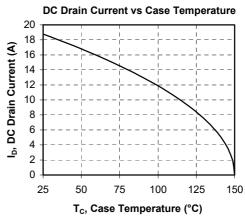
Typical Performance Curve



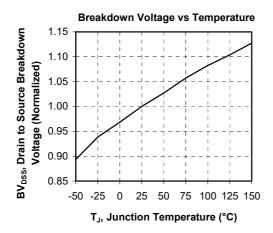


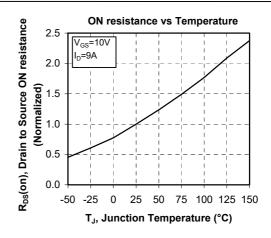


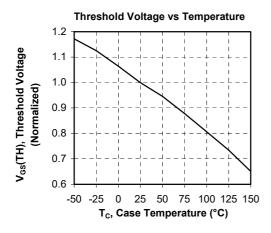


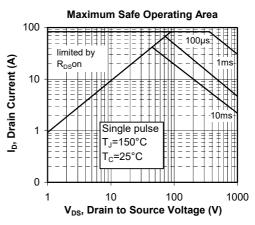


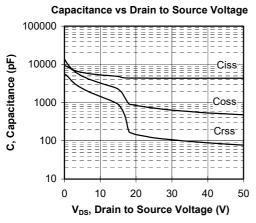


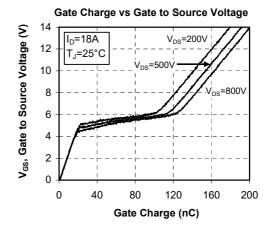




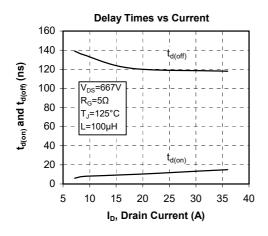


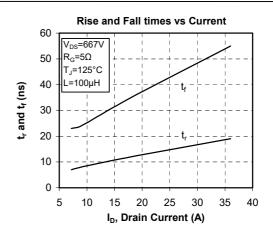


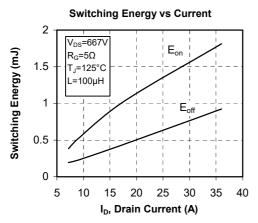


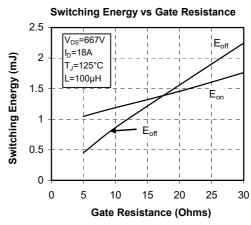


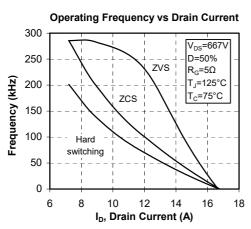


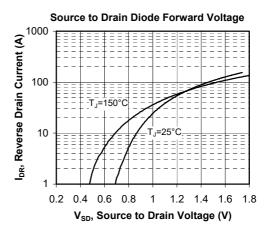












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